

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241723US2S		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Shigeru NAGASAKA, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
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	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
AW		M. Togo, et al., "Low-Leakage and Highly-Reliable 1.5nm SiON Gate-Dielectric Using Radical Oxynitridation for Sub-0.1µm CMOS", Silicon Systems Research Labs., NEC.C (Japan), 2000 SYMPOSIUM ON VLSI TECHNOLOGY DIGEST OF TECHNICAL PAPERS, 2000, pgs. 116-117					
AX		Wei-Hua Liu, et al., "A-2 Transistor Source-select (2TS) Flash EEPROM for 1.8V-Only Applications", Semiconductor Technologies Laboratory, Motorola Inc., Austin, Texas, NON-VOLATILE SEMICONDUCTOR MEMORY WORKSHOPS 4.1, 1997, pgs. 1-3					
AY							
AZ						<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>[Signature]</i>					Date Considered 4/28/05		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							